

L Number	Hits	Search Text	DB	Time stamp
-	10	LISENKER-B LISENKER-BORIS-S LISENKER-B-S	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/16 09:49
-	3	JANKELEVICH	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/02 08:30
-	32	KIZILYALLI and deuter\$8	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/16 09:52
-	3684	438/301.ccls. 438/303.ccls. 438/595.ccls. 438/786.ccls. 438/791.ccls. 427/255.29.ccls. 427/255.39.ccls. 427/255.393.ccls. 427/255.394.ccls.	USPAT; US-PGPUB	2004/09/16 09:50
-	1569	deuter\$8 and (cvd (chemical adj vapor) tetrachlorosilane tcs "sicl.sub.4" hexadichlorosilane hcd "si.sub.2 cl.sub.6" "si.sub.2cl.sub.6")	USPAT; US-PGPUB	2004/09/16 10:00
-	12	(438/301.ccls. 438/303.ccls. 438/595.ccls. 438/786.ccls. 438/791.ccls. 427/255.29.ccls. 427/255.39.ccls. 427/255.393.ccls. 427/255.394.ccls.) and deuter\$8	USPAT; US-PGPUB	2004/09/16 10:06
-	11	deuter\$8 and (tetrachlorosilane tcs "sicl.sub.4" hexachlorodisilane hcd "si.sub.2 cl.sub.6" "si.sub.2cl.sub.6")	EPO; JPO; DERWENT; IBM_TDB	2004/09/16 11:06
-	143	deuter\$8 and (cvd (chemical adj vapor)) and (tetrachlorosilane tcs "sicl.sub.4" hexachlorodisilane hcd "si.sub.2 cl.sub.6" "si.sub.2cl.sub.6")	USPAT; US-PGPUB	2004/09/16 11:14
-	28	deuter\$8 and ((silicon adj (oxynitride nitride)) sion sio?n? si?n? "si.sub.3 n.sub.4" "si.sub.3n.sub.4")	EPO; JPO; DERWENT; IBM_TDB	2004/09/17 08:00
-	51	deuter\$8 same (cvd (chemical adj vapor)) same ((silicon adj (oxynitride nitride)) sion sio?n? si?n? "si.sub.3 n.sub.4" "si.sub.3n.sub.4")	USPAT; US-PGPUB	2004/09/16 14:02
-	8	deuter\$8 and ((silicon adj oxynitride) sino sion sio?n? "sio.sub.xn.sub.y" "sio.sub.x n.sub.y" "sin.sub.xo.sub.y" "sin.sub.x o.sub.y" "si.sub.xo.sub.yn.sub.z" "si.sub.x o.sub.y n.sub.z" "si.sub.xn.sub.yo.sub.z" "si.sub.x n.sub.y o.sub.z")	EPO; JPO; DERWENT; IBM_TDB	2004/09/17 08:24
-	29	deuter\$8 same ((silicon adj oxynitride) sino sion sio?n? "sio.sub.xn.sub.y" "sio.sub.x n.sub.y" "sin.sub.xo.sub.y" "sin.sub.x o.sub.y" "si.sub.xo.sub.yn.sub.z" "si.sub.x o.sub.y n.sub.z" "si.sub.xn.sub.yo.sub.z" "si.sub.x n.sub.y o.sub.z")	USPAT; US-PGPUB	2004/09/17 08:24
-	137	(spacer near nitride) same (etch\$6 with (gas dry vertical\$4 anisotropic\$8)) same ((source drain) with implant\$8) ((spacer near nitride) same (etch\$6 with (gas dry vertical\$4 anisotropic\$8)) same ((source drain) with implant\$8)) and dram	USPAT; US-PGPUB	2004/09/17 10:37
-	49		USPAT; US-PGPUB	2004/09/17 10:37